



Product data sheet

1. Product profile

1.1 General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

1.2 Features and benefits

- Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss

1.3 Applications

 Output rectifiers in high-frequency switched-mode power supplies

1.4 Quick reference data

- Low thermal resistance
- Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	200	V
I _{F(AV)}	average forward current	square-wave pulse; δ = 0.5 ; T _{mb} ≤ 128 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	8	А
Static cha	aracteristics					
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; see <u>Figure 4</u>	-	0.8	0.895	V
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 1 A$; $V_R = 30 V$; $dI_F/dt = 100 A/s$; $T_j = 25 °C$; ramp recovery; see <u>Figure 5</u> ; see <u>Figure 7</u>	-	20	25	ns
Electrost	atic discharge					
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ	-	-	8	kV



Pinning information 2.

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode	mb	K — A 001aaa020
mb	mb	mounting base; cathode		

SOD59 (TO-220AC)

Ordering information 3.

Table 3. **Ordering information**

Type number	r Package		
	Name	Description	Version
BYW29E-200	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

Limiting values 4.

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	200	V
V _{RWM}	crest working reverse voltage		-	200	V
V _R	reverse voltage		-	200	V
I _{F(AV)}	average forward current	square-wave pulse; δ = 0.5 ; T _{mb} ≤ 128 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	8	А
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 128 °C	-	16	A
I _{FSM}	non-repetitive peak forward	t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	88	А
	current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	80	А
I _{RRM}	repetitive peak reverse current	$\delta = 0.001$; t _p = 2 µs	-	0.2	А
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs	-	0.2	А
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C
Electrosta	tic discharge				
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ	-	8	kV

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BYW29E-200

Ultrafast power diode

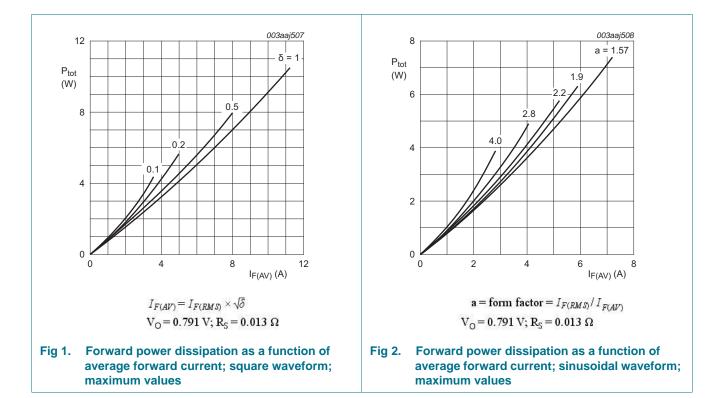
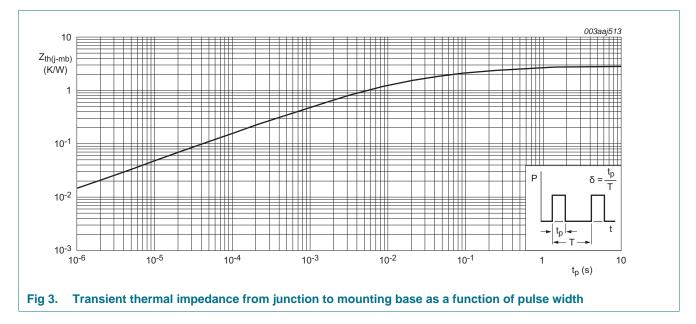


Table C

5. Thermal characteristics

Thermal characteristics

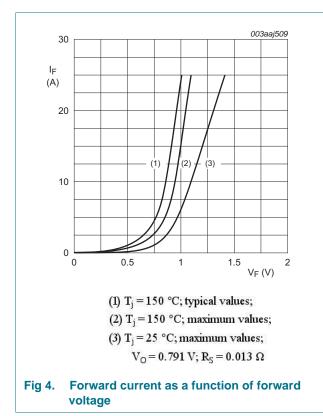
Table 5.	i nermai characterístics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 3	-	-	2.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

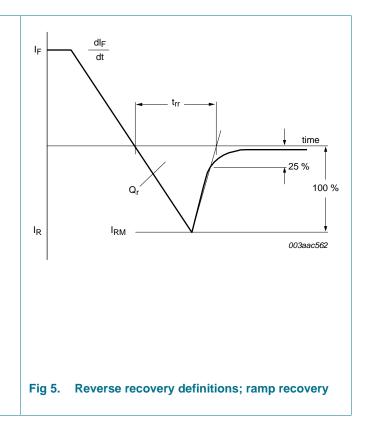


Ultrafast power diode

6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; see <u>Figure 4</u>	-	0.92	1.05	V
		$I_F = 20 \text{ A}; T_j = 25 \text{ °C}; \text{ see } Figure 4$	-	1.1	1.3	V
		$I_F = 8 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 4}}{\text{Figure 4}}$	-	0.8	0.895	V
I _R	reverse current	V _R = 200 V; T _j = 25 °C	-	2	10	μΑ
		V _R = 200 V; T _j = 100 °C	-	0.2	0.6	mA
Dynamic	characteristics					
Qr	recovered charge	I _F = 2 A; V _R = 30 V; dI _F /dt = 20 A/s; T _j = 25 °C; see <u>Figure 5</u> ; see <u>Figure 6</u>	-	4	11	nC
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/s; ramp recovery; T _j = 25 °C; see <u>Figure 5</u> ; see <u>Figure 7</u>	-	20	25	ns
		$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; \text{ step recovery}; \\I_{R(\text{meas})} = 0.25 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{\text{Figure 8}}$	-	15	20	ns
V _{FRM}	forward recovery voltage	I _F = 1 A; dI _F /dt = 10 A/s; T _j = 25 °C; see <u>Figure 9</u>	-	1	-	V

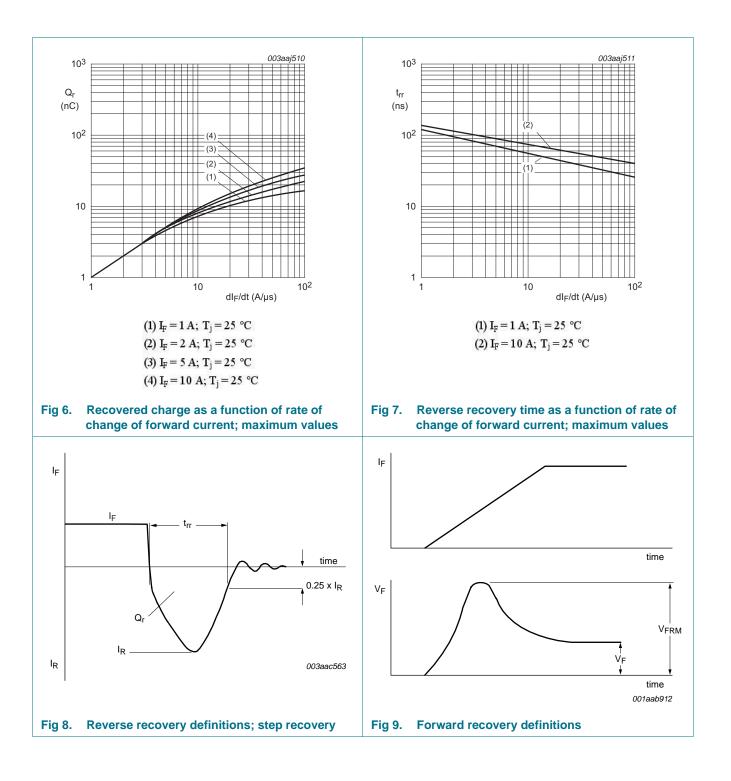




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BYW29E-200

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7. Package outline

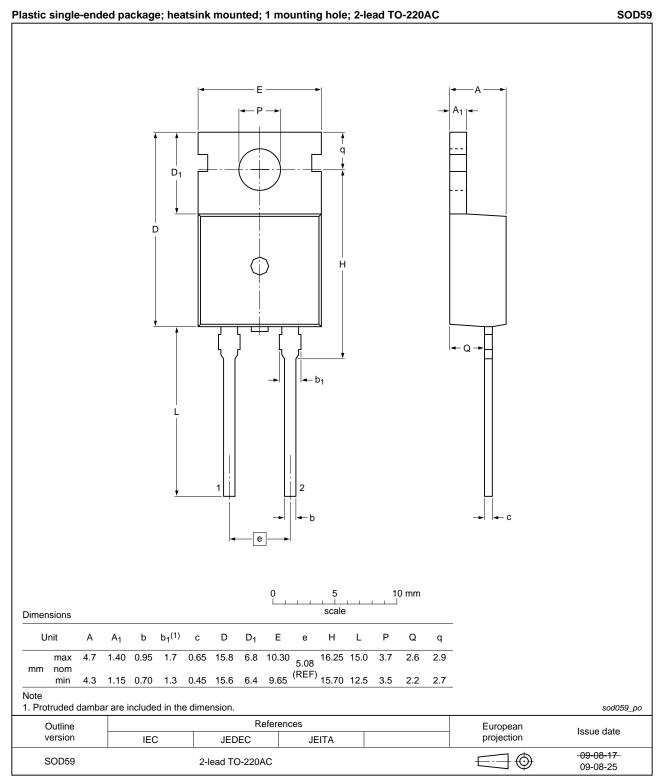


Fig 10. Package outline SOD59 (TO-220AC)

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8. Revision history

Table 7. Revision hi	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BYW29E-200 v.5	20120320	Product data sheet	-	BYW29E_SERIES v.4
Modifications:	 The format of this of NXP Semiconduct 	document has been redes ors.	igned to comply with the r	new identity guidelines of
	 Legal texts have be 	een adapted to the new c	ompany name where app	propriate.
BYW29E_SERIES v.4	20010801	Product data sheet	-	BYW29E_SERIES v.3

Legal information 9.

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Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions'

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